Elektronische Bauelemente

CMPSH-3/ -3A/ -3C/ -3S

VOLTAGE 30V

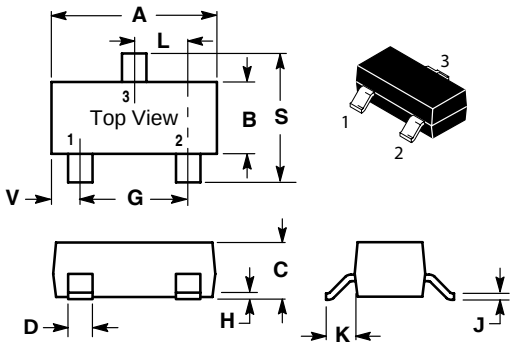
Surface Mount Schottky Barrier Rectifiers Array

RoHS Compliant Product

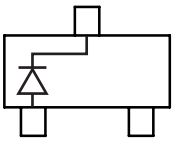
A suffix of "-C" specifies halogen & lead-free

FEATURES

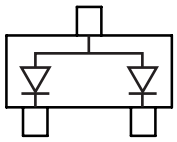
- Low forward voltage
- Fast switching



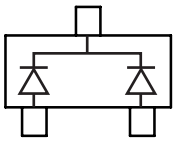
SOT-23		
Dim	**Min**	**Max**
A	2.800	3.040
B	1.200	1.400
C	0.890	1.110
D	0.370	0.500
G	1.780	2.040
H	0.013	0.100
J	0.085	0.177
K	0.450	0.600
L	0.890	1.020
S	2.100	2.500
V	0.450	0.600
All Dimension in mm		



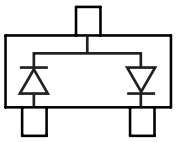
CMPSH-3
Marking: D95



CMPSH-3A
Marking: DB1



CMPSH-3C
Marking: DB2



CMPSH-3S
Marking: DA5

MAXIMUM RATINGS @ T_A = 25 °C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak Reverse Voltage Working peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
Forward Continuous Current	I_{FM}	100	mA
Power Dissipation	P_D	350	mW
Thermal Resistance	$R_{\theta JA}$	357	°C/W
Junction and Storage Temperature	T_J, T_{STG}	150, -55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (Tamb = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)}$	I_R = 100 μA		30	V
Reverse Voltage Leakage Current	I_R	V_R = 25 V, T_A = 25 °C		500	nA
		V_R = 25 V, T_A = 100 °C		100	μA
Forward Voltage	V_F	I_F = 2 mA I_F = 15 mA I_F = 100 mA		0.33 0.45 1	V
Diode Capacitance	C_{tot}	V_R = 1V, f = 1MHz	7		pF
Junction and Storage Temperature	t_{ff},	I_F = I_R = 10mA I_{RR} = 1mA, R_L=100Ω		5	Ns

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ELECTRICAL CHARACTERISTICS CURVES